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View Online at https://aerobasegroup.com/nsn/5961-01-102-7808

Inclosure Material:

Metal

Overall Length:

0.650 inches

Overall Height:

0.190 inches

Overall Width:

0.420 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-220ab

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

45.0 collector to base voltage/static/emitter open and 5.0 emitter to base voltage, static, collector open and 45.0 collector to emitter voltage/static/base open

Current Rating Per Characteristic:

4.00 amperes source cutoff current and 1.00 amperes source cutoff current

Power Rating Per Characteristic:

40.0 watts small-signal input power, common-collector

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

3 tab, solder lug

Specification Data:

80131-release6295 professional/industrial association specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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Fiig: A110a0

